

IN THE CLAIMS:

Please amend Claim 1 as follows:

1. (Currently amended) A sensor integrated on a single semiconductor substrate, comprising:
 - a sensor block including a pixel unit and a scanning unit for selecting a pixel of the pixel unit, the pixel unit comprising a plurality of pixels each including a light-receiving element;
 - a signal processing block for processing a signal output from said sensor block;
 - a single electric power voltage input terminal for externally inputting an electric power voltage from outside of the substrate; and
 - a voltage supply unit for supplying a first voltage to the sensor block, and for supplying a second voltage to the signal processing block, wherein the second voltage is smaller in amplitude than the first voltage, and wherein the voltage supply unit is supplied with electric power from a single power source disposed externally of the semiconductor substrate ~~control circuit arranged on the substrate, for generating a plurality of different voltages from the electric power voltage externally input at the single electric power voltage input terminal, to make a power supply voltage or an amplitude or high level of a clock signal used in said sensor block higher than a power supply voltage of said signal processing block.~~

2. (Original) A sensor according to Claim 1, wherein a gate insulating

layer of at least some insulated gate transistors of said sensor block is thicker than that of an insulated gate transistor used in said signal processing block.

3. (Original) A sensor according to Claim 1, wherein a well density of at least some insulated gate transistors of said sensor block is lower than that of an insulated gate transistor used in said signal processing block.

4. (Original) A sensor according to Claim 1, wherein a threshold voltage of at least some insulated gate transistors of said sensor block is higher than that of an insulated gate transistor used in said signal processing block.

5. (Previously Presented) A sensor according to Claim 1, wherein the light-receiving element is a buried photodiode.

6. (Previously Presented) A sensor according to Claim 5, wherein the pixel has a charge/voltage conversion unit which is connected to the buried photodiode through a transfer switch.

7. (Previously Presented) A sensor according to Claim 1, wherein said sensor block and said signal processing block are connected via a level shift circuit for shifting a signal level.

8. (Original) A sensor according to Claim 1, wherein said signal processing block comprises an A/D conversion circuit for converting an analog signal into a

digital signal.

9. (Previously Presented) A sensor according to Claim 8, wherein said signal processing block comprises a signal processing circuit for forming a luminance signal and a chrominance signal.

10.-20. (Cancelled)